TM 2826

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&LIONE

IN THE UNITED STATES PATENT AND TRADEMARK OFFICE

In re Appln. of: Ko, et al.

Appln. No.: 10/502,110

Filed: July 21, 2004

For: PLANAR AVALANCHE
PHOTODIODE

Attorney Docket No: 10555-085

Examiner:

Art Unit: 2826

Mail Stop Amendment
Commissioner for Patents
P. O. Box 1450
Alexandria, VA 22313-1450

TRANSMITTAL

Sir:

Attached is/are:

☒ Second Supplemental Information Disclosure Statement and 1 Sheet of Form PTO-1449, and 5 required references

☒ Return Receipt Postcard

Fee calculation:

☒ No additional fee is required.

☐ Small Entity.

☐ An extension fee in an amount of $_____ for a _____-month extension of time under 37 C.F.R. § 1.136(a).

☐ A petition or processing fee in an amount of $_____ under 37 C.F.R. § 1.17(_____).

☐ An additional filing fee has been calculated as shown below:

	Claims Remaining After Amendment		Highest No. Previously Paid For	Present Extra	Small Entity		or	Not a Small Entity	
					Rate	Add'l Fee		Rate	Add'l Fee
Total		Minus			x $9=			x $18=	
Indep.		Minus			x $43=			x $86=	
First Presentation of Multiple Dep. Claim					+$145=			+ $290=	
					Total	$		Total	$

Fee payment:

☐ A check in the amount of $_____ to cover the above-identified fee(s) is enclosed.

☐ Please charge Deposit Account No. 23-1925 in the amount of $_____ . A copy of this Transmittal is enclosed for this purpose.

☐ Payment by credit card in the amount of $_____ (Form PTO-2038 is attached).

☒ The Director is hereby authorized to charge payment of any additional filing fees required under 37 CFR § 1.16 and any patent application processing fees under 37 CFR § 1.17 associated with this paper (including any extension fee required to ensure that this paper is timely filed), or to credit any overpayment, to Deposit Account No. 23-1925.

Respectfully submitted,

February 24, 2006
Date

John M. Card (Reg. No. 48,423)

IN THE UNITED STATES PATENT AND TRADEMARK OFFICE

In re Appln. of: KO ET AL.

Appln. No.:   10/502,110

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SECOND SUPPLEMENTAL INFORMATION DISCLOSURE STATEMENT

In accordance with the duty of disclosure under 37 C.F.R. §1.56 and §§1.97-1.98, and more particularly in accordance with 37 C.F.R. §1.97(b), Applicants hereby cite the following reference(s):

No.	Date of Publication	Patentee/Applicant/Assignee
6,104,047	08/2000	Watanabe
6,635,908	10/2003	Tanaka, et al.
M.A. Itzler, C.S. Wang, S. McCoy, N. Codd and N. Komba, Planar bulk InP avalanche photodiode design for 2.5 and 10Gb/s applications, Proc 24th ECOC 1998, paper MoB03		
L.E. Tarof, J. Yu, R. Bruce, D.G. Knight, T. Baird and B. Oosterbrink, High frequency performance of separate absorption grading charge and multiplication InP/InGaAs avalanche photodiodes, IEEE Photon. Technol. Lett. 5, 672-674, 1993		
Watanabe, T. Nakata, M. Tsuji, K. Makita, K. Taguchi, High reliability and low dark current 10 Gb/s planar superlattice avalanche photodiodes, IEEE Photon. Technol. Lett. 9, 1619-1621, 1997		
J.C. Campbell, S. Demiquel, F. Ma, A. Beck, X. Guo, S. Wang, X. Zeng, X. Li, J.D. Beck, M.A. Kinch, A. Huntington, L.A. Coldren, J. Decobert, N. Tscherptner, Recent advances in avalanche photodiodes, IEEE J. Select. Topics Quantum Electron., 10, 777-787, 2004		
R.R. Sutherland, C.P. Skrimshire, M.J. Robertson, A reliability methodology applied to very high reliability planar InGaAs/InP PIN photodetectors, Br. Telecom. Technol. J., 7, 69-77, Jan. 1989		

Applicants are enclosing Form PTO-1449 (one sheet), along with a copy of each listed reference for which a copy is required under 37 C.F.R. §1.98(a)(2). As each of the listed references is in English, no further commentary is believed to be necessary,

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37 C.F.R §1.98(a)(3). Applicants respectfully request the Examiner's consideration of the above reference(s) and entry thereof into the record of this application.

By submitting this Statement, Applicants are attempting to fully comply with the duty of candor and good faith mandated by 37 C.F.R. §1.56. As such, this Statement is not intended to constitute an admission that any of the enclosed references, or other information referred to therein, constitutes "prior art" or is otherwise "material to patentability," as that phrase is defined in 37 C.F.R. §1.56(a).

Applicants have calculated no fee to be due in connection with the filing of this Statement. However, the Director is authorized to charge any fee deficiency associated with the filing of this Statement to a deposit account, as authorized in the Transmittal accompanying this Statement.

Respectfully submitted,

2/24/06
Date

John M. Card (Reg. No.48,423)

FORM PTO-1449			APPLICATION NO. 10/502,110		CASE NO. 10555-085	
LIST OF PATENTS AND PUBLICATIONS FOR APPLICANT'S INFORMATION DISCLOSURE STATEMENT			FILING DATE July 21, 2004		ART UNIT 2826	
			APPLICANT(S): Ko, et al.			

REFERENCE DESIGNATION   U.S. PATENT DOCUMENTS

EXAMINER INITIAL		DOCUMENT NUMBER	DATE	NAME	CLASS/ SUBCLASS	FILING DATE
		6,104,047	08/2000	Watanabe		
		6,635,908	10/2003	Tanaka, et al.		

FOREIGN PATENT DOCUMENTS

EXAMINER INITIAL		DOCUMENT NUMBER	DATE	COUNTRY	CLASS/ SUBCLASS	TRANSLATION YES	NO

EXAMINER INITIAL		OTHER ART (Including Author, Title, Date, Pertinent Pages, etc.)
		M.A. Itzler, C.S. Wang, S. McCoy, N. Codd and N. Komba, Planar bulk InP avalanche photodiode design for 2.5 and 10Gb/s applications, Proc 24th ECOC 1998, paper MoB03
		L.E. Tarof, J. Yu, R. Bruce, D.G. Knight, T. Baird and B. Oosterbrink, High frequency performance of separate absorption grading charge and multiplication InP/InGaAs avalanche photodiodes, IEEE Photon. Technol. Lett. 5, 672-674, 1993
		Watanabe, T. Nakata, M. Tsuji, K. Makita, K. Taguchi, High reliability and low dark current 10 Gb/s planar superlattice avalanche photodiodes, IEEE Photon. Technol. Lett. 9, 1619-1621, 1997
		J.C. Campbell, S. Demiquel, F. Ma, A. Beck, X. Guo, S. Wang, X. Zeng, X. Li, J.D. Beck, M.A. Kinch, A. Huntington, L.A. Coldren, J. Decobert, N. Tscherptner, Recent advances in avalanche photodiodes, IEEE J. Select. Topics Quantum Electron., 10, 777-787, 2004
		R.R. Sutherland, C.P. Skrimshire, M.J. Robertson, A reliability methodology applied to very high reliability planar InGaAs/InP PIN photodetectors, Br. Telecom. Technol. J., 7, 69-77, Jan. 1989

EXAMINER	DATE CONSIDERED

EXAMINER: Initial if reference considered, whether or not citation is in conformance with MPEP 609; Draw line through citation if not in conformance and not considered. Include copy of this form with next communication to applicant.